

2SD2136 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 1.25 W ($T_{amb}=25^{\circ}C$)

Collector current

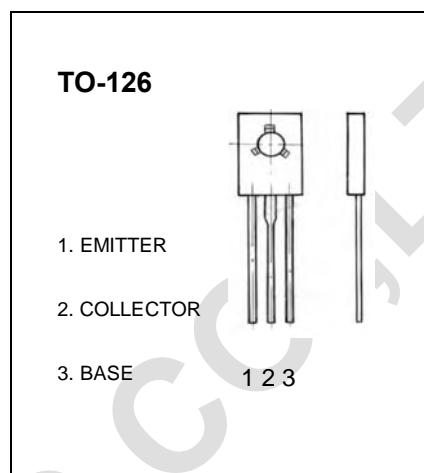
I_{CM} : 3 A

Collector-base voltage

$V_{(BR)CBO}$: 60 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=30mA, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$			200	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6V, I_C=0$			1	mA
DC current gain	$h_{FE(1)}$	$V_{CE}=4V, I_C=1A$	40		250	
	$h_{FE(2)}$	$V_{CE}=4V, I_C=3A$	10			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=3A, I_B=375mA$			1.2	V
Base-emitter voltage	V_{BE}	$V_{CE}=4V, I_C=3A$			1.8	V
Transition frequency	f_T	$V_{CE}=5V, I_C=0.1A, f=200MHz$		30		MHz
Switch Time	Turn-on time	$I_C=1A, I_{B1}=0.1A, I_{B2}=-0.1A$		0.5		μs
	Storage time			2.5		μs
	Fall time			0.4		μs

CLASSIFICATION OF $h_{FE(1)}$

Rank	P	Q	R
Range	40-90	70-150	120-250